



AFRL-RZ-WP-TP-2012-0156

**IMPACT OF EDGE-BARRIER PINNING IN
SUPERCONDUCTING THIN FILMS (POSTPRINT)**

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FEBRUARY 2012

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WRIGHT-PATTERSON AIR FORCE BASE, OH 45433-7251
AIR FORCE MATERIEL COMMAND
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REPORT DOCUMENTATION PAGE

Form Approved
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1. REPORT DATE (DD-MM-YY) February 2012	2. REPORT TYPE Journal Article Postprint	3. DATES COVERED (From - To) 01 March 2008 – 01 March 2010
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4. TITLE AND SUBTITLE IMPACT OF EDGE-BARRIER PINNING IN SUPERCONDUCTING THIN FILMS (POSTPRINT)	5a. CONTRACT NUMBER In-house
	5b. GRANT NUMBER
	5c. PROGRAM ELEMENT NUMBER 62203F

6. AUTHOR(S) W.A. Jones and M.J. Mullins (University of Dayton) P.N. Barnes and T.J. Haugan (AFRL/RZPG) F.J. Baca (Los Alamos National Laboratory) R.L.S. Emergo and J. Wu (University of Kansas) J.R. Clem (Iowa State University)	5d. PROJECT NUMBER 3145
	5e. TASK NUMBER 32
	5f. WORK UNIT NUMBER 314532ZE

7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES) University of Dayton Dayton, OH 45469 ----- Mechanical Energy Conversion Branch (AFRL/RZPG) Energy/Power/Thermal Division Air Force Research Laboratory, Propulsion Directorate Wright-Patterson Air Force Base, OH 45433-7251 Air Force Materiel Command, United States Air Force	Los Alamos National Laboratory Los Alamos, NM 87545 ----- University of Kansas Department of Physics and Astronomy Lawrence, KS 66045 ----- Iowa State University Department of Physics and Astronomy and Ames Laboratory Ames, IA 50011-3160	8. PERFORMING ORGANIZATION REPORT NUMBER AFRL-RZ-WP-TP-2012-0156
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9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES) Air Force Research Laboratory Propulsion Directorate Wright-Patterson Air Force Base, OH 45433-7251 Air Force Materiel Command United States Air Force	10. SPONSORING/MONITORING AGENCY ACRONYM(S) AFRL/RZPG 11. SPONSORING/MONITORING AGENCY REPORT NUMBER(S) AFRL-RZ-WP-TP-2012-0156
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12. DISTRIBUTION/AVAILABILITY STATEMENT
Approved for public release; distribution unlimited.

13. SUPPLEMENTARY NOTES
Journal article published *Applied Physics Letters*, Vol. 97, No. 1, 2010.
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PA Case Number: 88ABW-2010-3362; Clearance Date: 01 Jan 2010. This paper has color content.

14. ABSTRACT
It has been suggested that edge-barrier pinning might cause the critical current density (J_c) in bridged superconducting films to increase. Subsequent work indicated that this edge-barrier effect does not impact bridges larger than $1\mu\text{m}$. However, we provide a theoretical assessment with supporting experimental data suggesting edge-barrier pinning can significantly enhance J_c for bridges of a few microns or even tens of microns thus skewing any comparisons among institutions. As such, when reporting flux pinning and superconductor processing improvements for J_c comparisons, the width of the sample has to be taken into consideration as is currently done with film thickness.

15. SUBJECT TERMS
barrier, pinning, edge, film, thickness, bridges, enhance, sample

16. SECURITY CLASSIFICATION OF:			17. LIMITATION OF ABSTRACT: SAR	18. NUMBER OF PAGES 10	19a. NAME OF RESPONSIBLE PERSON (Monitor) Timothy J. Haugan 19b. TELEPHONE NUMBER (Include Area Code) N/A
a. REPORT Unclassified	b. ABSTRACT Unclassified	c. THIS PAGE Unclassified			

1 Impact of edge-barrier pinning in superconducting thin films

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10 (Received 16 September 2010; accepted 1 December 2010; published online xx xx xxxx)

11 It has been suggested that edge-barrier pinning might cause the critical current density (J_c) in
 12 bridged superconducting films to increase. Subsequent work indicated that this edge-barrier effect
 13 does not impact bridges larger than 1 μm . However, we provide a theoretical assessment with
 14 supporting experimental data suggesting edge-barrier pinning can significantly enhance J_c for
 15 bridges of a few microns or even tens of microns thus skewing any comparisons among institutions.
 16 As such, when reporting flux pinning and superconductor processing improvements for J_c
 17 comparisons, the width of the sample has to be taken into consideration as is currently done with
 18 film thickness. © 2010 American Institute of Physics. [doi:10.1063/1.3529945]

20 Enhancing the critical current density (J_c) of a supercon-
 21 ducting film has been a major effort in high temperature
 22 superconductors (HTS). Recent efforts have been focused on
 23 raising the J_c of type-II HTS thin films via the introduction
 24 of particulate and columnar flux pinning centers, especially
 25 in $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ (YBCO).¹⁻⁸ To evaluate the effectiveness of
 26 these pinning centers made at the various institutions, the
 27 data are often compared with each other. However, the
 28 samples' geometric sizes can distort the comparisons, mak-
 29 ing it difficult to ascertain the relative improvement in a
 30 straightforward manner. For example, it is well known that
 31 the J_c of these thin superconductor coatings will decline as
 32 the sample thickness increases.⁹ Most researchers conceptu-
 33 ally account for this sample-thickness dependence when
 34 comparing J_c values.

35 In order to measure the J_c , superconducting strips are
 36 often cut with narrow bridges (5–20 μm , for example) to
 37 allow for more accurate measurements. It is of interest that
 38 narrower bridges tend to yield higher J_c 's. While this may
 39 initially be ascribed to sample inhomogeneity, vast improve-
 40 ments in uniformity of the sample do not seem to alter this
 41 trend. It has been previously reported that the HTS sample
 42 edge can effectively provide a barrier to magnetic flux delay-
 43 ing its penetration into the sample.¹⁰⁻¹³ This is true even if
 44 the vortices in the interior of the thin film are completely
 45 unpinned as in the case of no bulk pinning in a sample. Thus,
 46 the geometrical edge barrier can have an impact on the over-
 47 all pinning affecting the properties of YBCO thin films.

48 Based on experimental observations, one group sug-
 49 gested that the edge barrier's pinning effect does enhance the
 50 J_c in narrow bridges,¹⁴ but a subsequent report concluded
 51 that this enhancement is negligible in widths greater than
 52 1 μm .¹⁵ The data in that report, however, were limited to
 53 just three samples. In light of this, the bridge width used to
 54 measure the J_c of a given HTS sample is often not consid-
 55 ered when data are reported. The work performed here pro-
 56 vides both a theoretical basis and a broader experimental

data set that demonstrates this edge-barrier enhancement is
 important at bridge widths up to tens of microns. This can
 explain the high J_c values consistently found in these nar-
 rowly bridged samples.

We consider a theoretical model by Elistratov *et al.*¹⁶ and
 extended by Benkraouda and Clem¹³ to calculate the relative
 pinning of the edge barrier. For this research, consider a su-
 perconducting strip centered on the z axis with width W
 ($|x| < W/2$) and thickness d , where W is much larger than the
 two dimensional screening length, $\Lambda = 2\lambda^2/d$. Here λ
 $= \lambda(0)/\sqrt{1 - (77\text{K}/T_c)^4}$ is the London penetration depth at
 temperature of 77 K. In our case the thickness d is somewhat
 larger than the London penetration depth λ , see Refs. 13 and
 17. The strip carries a total current I in the z direction. Then
 for a strip containing no magnetic flux and with no applied
 magnetic field, the sheet current density $K(x)$ in the z direc-
 tion is simply determined by the Meissner-state current
 density generated by the applied current I , $K(x)$
 $= I/\pi\sqrt{(W/2)^2 - x^2}$.

With no applied field ($H_a=0$) we can account for the
 edge barrier with the equation $I_{s0} \approx \pi K_s \sqrt{W\Lambda}$ where I_{s0} is the
 geometrical-barrier critical current in absence of bulk pin-
 ning and K_s is the sheet current density at which vortices
 nucleate and enter the superconductor and the barrier is over-
 come. For an ideal edge $K_s = j_{\text{GL}}d$, where j_{GL} is the
 Ginzburg–Landau depairing current density. Since an edge is
 inevitably not perfect, this provides a maximum pinning
 force. However, j_{GL} can be scaled to experimental data to
 account for the nonideal edge.

Using the temperature dependent depairing current
 density¹⁸⁻²⁰

$$j_{\text{GL}}(T) = \Phi_0/[3^{3/2}\pi\mu_0\lambda(T)^2\xi(T)] \quad (1)$$

the equations from Elistratov *et al.* can be solved in terms of
 width and temperature. Incorporating a dimensionless pa-
 rameter $p = I_p/I_{s0}$, we can characterize the critical current I_c
 for when $p < (\pi/2)$, the strip is vortex free and the edge
 barrier dominates ($I_c = I_{s0}$), and when $p > (\pi/2)$, the critical

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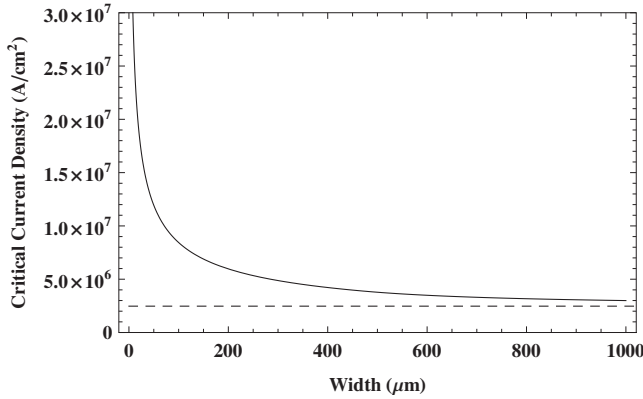


FIG. 1. The dotted line represents J_p and the solid curve represents the calculated J_c assuming a perfect edge. This curve represents the maximum J_c enhancement the edge barrier can have on a superconducting strip. Both curves are plotted for $T=77$ K. Note that as the bridge width increases, the true J_c asymptotically approaches the value of J_p . For this plot we used the empirically derived equation $J_p(T)=c(1-t^a)^b$, $c=7 \times 10^7$, $a=9/10$, $b=7/4$, $t=T/T_c=77/92$.

94 current is dependent on the combined edge barrier and bulk
95 pinning effects. The critical current is found by simulta-
96 neously solving the equations¹⁶

$$97 \quad 1 = (1 - b) \sqrt{\frac{1+a}{1-a}} \Pi\left(\frac{b-a}{1-a}, q\right) p \quad (2)$$

98 and

$$99 \quad 1 = (1 + a) \sqrt{\frac{1-b}{1+b}} \Pi\left(\frac{b-a}{1+b}, q\right) p \quad (3)$$

100 for a and b where $q=W(b-a)/(W/2-a)(W/2+b)$ and Π is
101 the complete elliptic integral of the third kind. The critical
102 current of the strip is then

$$103 \quad I_c(p) = \left(-\frac{a+b}{2\sqrt{(1-a)(1-b)}} + \frac{p}{2} \sqrt{\frac{1+b}{1-a}} \{(1-a)E(q) \right. \\ 104 \quad \left. + (1+a)K(q)\} \right) \times I_{s0}, \quad (4)$$

105 where a and b are the results of simultaneously solving Eqs.
106 (2) and (3). Here $E(q)$ and $K(q)$ represent the complete el-
107 liptic integral of the second and first kind, respectively.

108 We can plot J_c as a function of width and compare it
109 with the critical current density (J_p) resulting only from bulk
110 pinning, i.e., ignoring edge-barrier effects, to determine how
111 much the edge barrier can enhance the critical current. From
112 Fig. 1, we can easily see that the sample width can play a
113 strong role in enhancing the critical current, even in bridges
114 as large as 200 μm assuming a perfect edge. It should also
115 be noted that for a nonzero applied magnetic field, not shown
116 here, the edge-barrier effect rapidly diminishes. This model-
117 ing suggests two possible experimental approaches, among
118 several potential, to demonstrate the effect. One is to repeat-
119 edly narrow a given bridged sample to smaller widths mea-
120 suring the J_c after each size; two, plot $J_c(T)$ curves for a
121 couple different bridge sizes on samples that have a similar
122 J_c prior to bridging. Each approach can lead to different ex-
123 perimental difficulties, as discussed later, but was used to
124 collect data in this work demonstrating the effect.

The details of the deposition conditions and processing¹²⁵
are given elsewhere.^{1,21} In short, strips of YBCO films were¹²⁶
produced via pulsed laser deposition on SrTiO₃ single crystal¹²⁷
substrates and annealed in a partial oxygen atmosphere.¹²⁸
Bridges were patterned and etched using standard photoli-¹²⁹
thography techniques. Critical current and transport J_c mea-¹³⁰
surements were made at 500 μm bridge width as a baseline¹³¹
value. The samples were then etched to 200, 100, and¹³²
50 μm , respectively, with measurements made after each¹³³
cut. The widths and film thickness of the microbridges made¹³⁴
by photolithography were measured typically 8–10 times in¹³⁵
different locations with a calibrated P15 KLA-Tencor pro-¹³⁶
filometer, www.kla-tencor.com, to obtain a representative¹³⁷
cross-section area with standard error less than 1%. By etch-¹³⁸
ing the same sample repeatedly differences of J_c due to¹³⁹
sample variance are avoided and provide a direct compari-¹⁴⁰
son. However, the repeated etching and measurement can¹⁴¹
and did result in sample failure, but when this occurred it¹⁴²
would only cause the sample's J_c to degrade; it would not¹⁴³
increase the value. This explains why more data exist at the¹⁴⁴
larger bridge sizes for the different samples.¹⁴⁵

Due to photolithographic equipment limitations, bridge¹⁴⁶
sizes below 50 μm were patterned using a focused ion¹⁴⁷
beam. Samples were cut using a constant aspect ratio¹⁴⁸
method, where the bridge length to width ratio is 4. The¹⁴⁹
same width progression as previous samples was attempted¹⁵⁰
but this resulted in very high failure rates due to ion implan-¹⁵¹
tation and the resulting YBCO degradation. This high failure¹⁵²
rate is similar to reports in the literature by other groups.^{22–24}¹⁵³
As such, only two usable data points were obtained having¹⁵⁴
widths of 10 and 11 μm .¹⁵⁵

For the second approach, bridged samples were created¹⁵⁶
from the same batch where the J_c of several “sister” samples¹⁵⁷
could be verified for uniformity. Previous work demonstrated¹⁵⁸
good uniformity of samples from the same deposition batch.¹⁵⁹
Minor differences would and did exist in sample J_c but¹⁶⁰
would be quantifiable in comparisons. Photolithography at¹⁶¹
other facilities (University of Kansas) allowed bridges to be¹⁶²
made at 2, 5, and 15 μm .¹⁶³

To ensure proper measurement of the cross-section for¹⁶⁴
an accurate determination of J_c , we followed the suggestion¹⁶⁵
of Ref. 15 and measured the resistance of the bridge to derive¹⁶⁶
its cross-sectional area. We also calculated the cross-¹⁶⁷
sectional area based on measurement of the bridge directly.¹⁶⁸
In the former case we assumed the same resistivity to deter-¹⁶⁹
mine the cross-sectional area and in the latter case we as-¹⁷⁰
sumed accurate measurement of the bridges narrowest cross-¹⁷¹
sectional area. Only in the narrowest bridge widths did the¹⁷²
two measurements vary in some noticeable fashion. Even so,¹⁷³
the data led to the same conclusion.¹⁷⁴

Figure 2 shows the normalized J_c versus bridge width¹⁷⁵
data collected for the first approach. Note that there is a¹⁷⁶
gradual increase in J_c as the sample bridge width decreases.¹⁷⁷
For the two samples that were bridged to a narrow bridge¹⁷⁸
size of a few microns without damage, a significant increase¹⁷⁹
is present in accordance with the theory. Using these initial¹⁸⁰
experimental data we collected, the theoretical curve was fit¹⁸¹
to data and plotted in Fig. 2, represented by the solid black¹⁸²
curve. The curve fit was done by taking $K_s = \sigma j_{GL} d$ instead of¹⁸³
taking $K_s = j_{GL} d$, where j_{GL} is calculated using Eq. (1). In this¹⁸⁴
case the value of σ is roughly 20%. This is reasonable in that¹⁸⁵
for the smallest samples that have previously been reported¹⁸⁶
were able to achieve close to 30% of the depairing current¹⁸⁷

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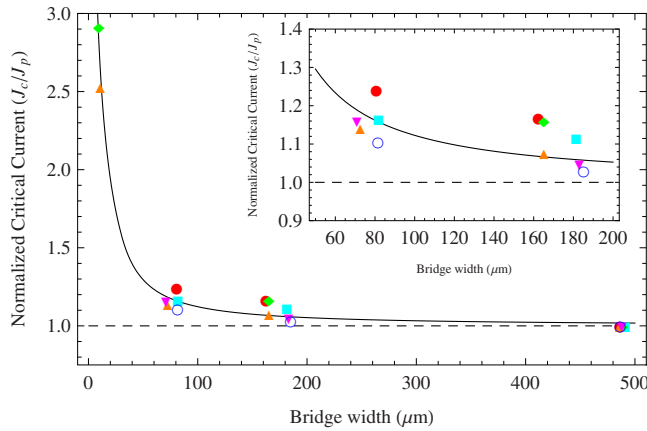


FIG. 2. (Color online) The black line represents the scaled J_c curve normalized by J_p . Markers of the same color and shape correspond to a single sample at different bridge widths. Data points are normalized with respect to the J_c of the 500 μm bridge, which were all in the range of 3–4.5 MA/cm². All measurements were done at 77.2 K and sample thickness is $\frac{1}{4}$ μm for each sample. In the above plot the Ginzburg–Landau depairing current density has been scaled by 0.2 for the theoretical curve. The inset is a simple magnification of the widths from 50 to 200 μm emphasizing that there is a significant J_c enhancement within this range.

188 density.²⁴ Although the edge is nonideal as expected and the
189 J_c improvement is less than maximum, it clearly plays a
190 strong role in bridges of tens of microns which are often used
191 by various research institutions.

192 For the second approach two samples with a similar J_c
193 were bridged to 2 and 5 μm and measured as a function of
194 temperature. According to the scaled theoretical curve given
195 in Fig. 2, a 58% enhancement should be seen in the 2 μm
196 bridge over that of the 5 μm bridge. The experimental re-
197 sults show an overall 61% enhancement thus supporting the
198 exponential increase in J_c for small bridge widths. A plot of
199 these two curves is provided in Fig. 3. All sister samples
200 from the same deposition were within 0.5 MA/cm² of each
201 other at 77 K and cannot account for the difference. Note that
202 this relative enhancement is over that of the 5 μm bridge
203 which would in turn be an enhancement over bridges of
204 500 μm . The key point is that both approaches used to
205 verify the edge-barrier effect suggests the importance of the
206 edge barrier in narrow bridge sizes.

207 The initial experimental data clearly suggest the pres-
208 ence of the edge barrier and is not contradicted by either

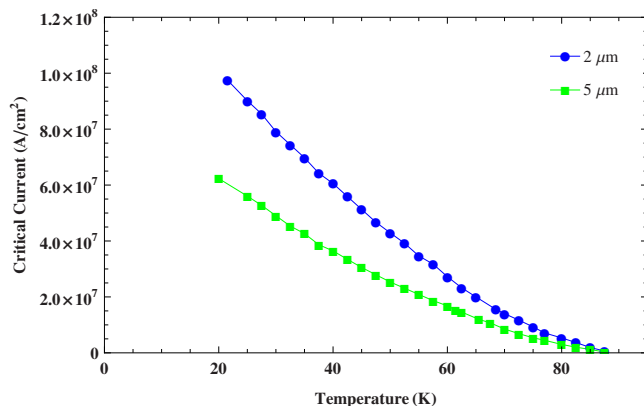


FIG. 3. (Color online) Measured transport $J_c(T)$ curves for bridges of 5 and 2 μm .

approach used. This concept is clearly critical to understand-
ing the true value of the pinning enhancement for institu-
tional comparisons, especially since often the bridge size
used to determine the J_c is not reported in publications. Nar-
row bridges of a few microns or even tens of microns can
greatly increase the critical current density (over 200% under
certain conditions) thus skewing any results for comparison.
As such the bridge width must be reported in addition to the
film thickness. The edge-barrier effect is more relevant to
self-field enhancement since it is negligible for most in-field
measurements.

The Air Force Office of Scientific Research supported
this work. We thank R. L. Dunning and J. A. Connors for
their help. The University of Kansas thanks the National Sci-
ence Foundation and the Department of Energy. Theoretical
work at the Ames Laboratory, Iowa State University, was
supported by the U.S. Department of Energy, Office of Basic
Energy Science, Division of Materials Sciences and Engi-
neering, under Contract No. DE-AC02-07CH11358.

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